ABSTRACT OF THE DISCLOSURE

A surface acoustic wave device is constructed by forming a piezoelectric thin film on a quartz substrate, and in such a manner that the electromechanical coupling coefficient for a Rayleigh wave, K^2, is enlarged. In this surface acoustic wave device, a piezoelectric thin film is disposed on a quartz substrate, and comb electrodes are disposed on the interface between the quartz substrate and the piezoelectric thin film. The normalized film thickness H/λ of the piezoelectric thin film is preferably at least about 0.05.